

Process for making polycrystalline silicon films for solar cells.

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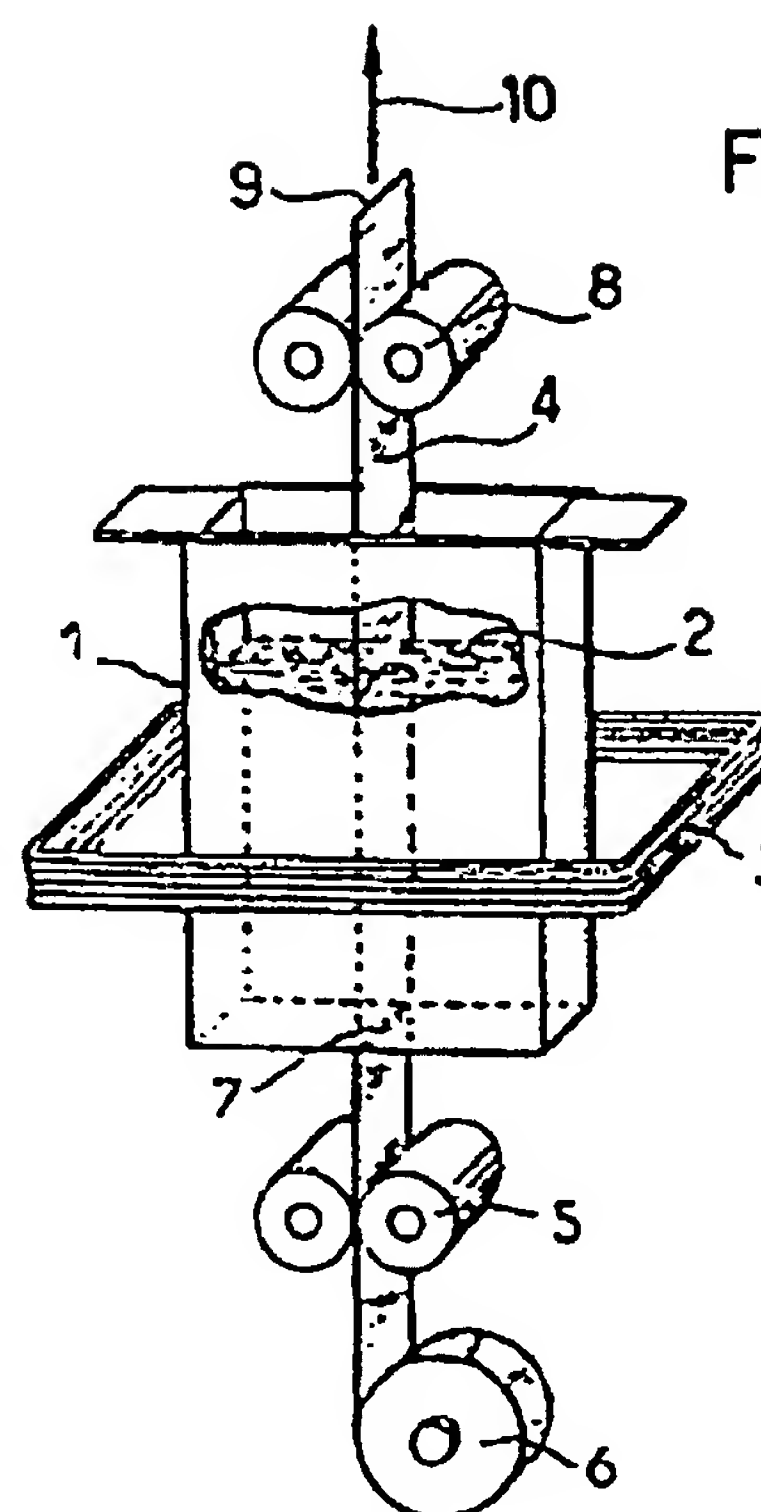
Cited documents:

FR2204457
FR2317005

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Abstract of EP0079567

1. A process for manufacturing polycrystalline silicon sheets for use in solar cells, consisting in :
- depositing a film of polycrystalline silicon over the entire surface of a carbon strip (4) by passing the strip through a bath (2) of molten silicon, characterized in that it further consists in :
- cutting off the edges of said strip (4) when covered with the silicon film so as to obtain a strip (11) comprising a respective layer (12, 13) of silicon on each side of a carbon sheet (14), and
- eliminating the carbon sheet by chemical or electrochemical oxidation so as to obtain two sheets of silicon.



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